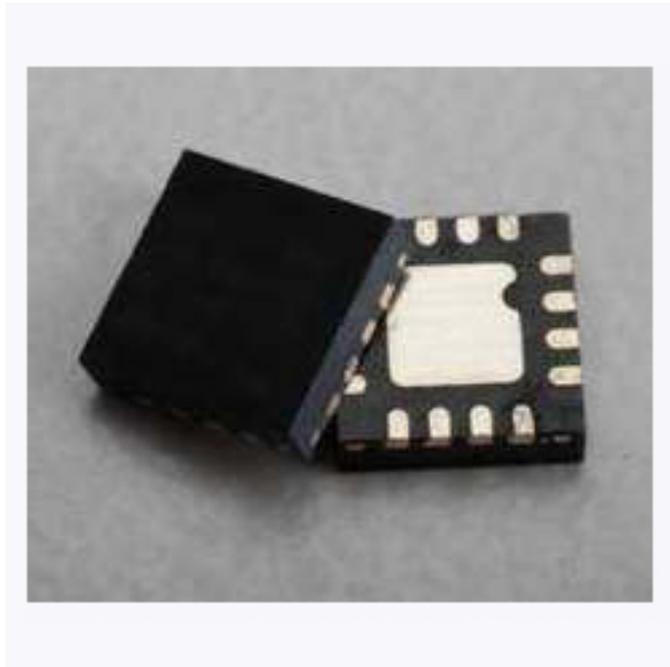


RFaxis Introduces Pure CMOS RF Front-End Platform



RFaxis, a fabless semiconductor company focused on innovative, next-generation RF solutions for the wireless and connectivity markets, today unveiled its next-generation pure CMOS RF Front-end Integrated Circuits (RFelC) platform to complement its current BiCMOS RFelC platform used to enable its portfolio of fully integrated, single-chip, single-die RF front-end solutions.

If the "Holy Grail" of integration for wireless connectivity is to deliver a complete wireless radio on a single CMOS silicon die, RFaxis' new pure CMOS RFelC platform enables a game-changing leap towards this goal.

"We leveraged our BiCMOS experience to accelerate the completion of our pure CMOS RFelC platform to provide our customers and investors a revolutionary sequel to our current portfolio of best-cost/best-quality RF front-end solutions, and to transform the RF front-end game once and for all," states Mike Neshat, president and CEO of RFaxis.

Dr. Oleksandr Gorbachov, CTO of RFaxis, goes on to explain, "Our RFelC platforms are essentially RF architectural templates that allow us to quickly spin-up new RF front-end solutions for compelling market opportunities for battery-operated wireless devices and for wireless devices with a continuous power supply. We are very excited about our pure CMOS RF front-end platform because it is a testimony that RFaxis is a true innovation leader."

Dr. Ping Peng, COO of RFaxis, adds, "Furthermore, our new pure CMOS platform is

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simply elegant, in that our new platform is architected for standard and proven 0.18 and 0.25 micron CMOS processes, and for abundant and inexpensive CMOS silicon material. This means our next-generation RFeICs based on this platform can be reliably and cost-effectively manufactured by a wide variety of major foundries globally."

Neshat continues, "We were told that a fully integrated RF front-end on a single-chip, single BiCMOS silicon die could not be done. Yet we are now manufacturing five major RFeIC lines to be launched in 2010. We were told that a fully integrated RF front-end on a single-chip, single pure CMOS silicon die was impossible. Yet we have proven that such a disruptive platform is viable and is available today only through RFaxis. We will continue to defy conventional thinking and bring to reality breakthrough innovations necessary to fuel the wireless movement."

"We have already achieved the best-cost/best-quality RF front-end solutions based on our BiCMOS RFeIC platform. When we unleash our portfolio of pure CMOS solutions in the summer of 2010, we will dramatically increase our value to our customers, partners, investors, and the wireless ecosystem," concludes Neshat.

The RFaxis BiCMOS RFeIC product lines available for delivery in early 2010 will be unveiled in time for the 2010 Consumer Electronics Show in January. More information regarding the RFaxis CMOS RFeIC product roadmap and delivery timetable is forthcoming.

About RFaxis, Inc.

Incorporated in January 2008, RFaxis, Inc. is an Irvine, California-based company specializing in the design and development of RF semiconductors. With its patent pending technologies, the company leads the way in next-generation wireless solutions designed for the multibillion dollar Bluetooth, WLAN, 802.11n/MIMO, Zigbee, WiMAX, and WHDI, and mobile phone (CDMA/WCDMA/EDGE/Evolved EDGE/LTE-3G/GSM) markets. Leveraging both BiCMOS and CMOS technology in conjunction with its own innovative inventions, RFaxis is home to the world's first RF Front-end Integrated Circuit (RFeIC). More information can be found at:

www.rfaxis.com [1]

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